Abstract

A semiconductor memory component such as a mask-programmable ROM component, has two memory cell transistors adjacent to each other in one column of a memory cell field. First and a second row-select/potential-equalization lines are equidistant from the two memory cell transistors and vertically above a diffusion region, which is assigned to both memory cell transistors. The first or the second row-select/potential-equalization line can be connected both to the word line of the first memory cell transistor and to the word line of the memory cell transistor of the second memory cell for equalizing the potential with one of the two word lines.